An Infineon Technologies Company

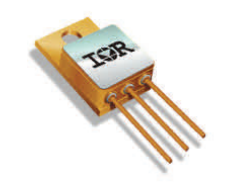
IRF5M5210

POWER MOSFET
THRU-HOLE (TO-254AA)

100V, P-CHANNEL
HEXFET MOSFET TECHNOLOGY

Product Summary

Part Number	$R_{DS(on)}$	I_D
IRF5M5210	0.07Ω	-34A



TO-254AA

Description

Fifth Generation HEXFET power MOSFETs from IR HiRel utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon unit area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

These devices are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high-energy pulse circuits.

Features

- Low $R_{DS(on)}$
- Avalanche Energy Ratings
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Light Weight

Absolute Maximum Ratings

	Parameter		Units
I_D @ V_{GS} = -10V, T_C = 25°C	Continuous Drain Current	-34	A
I_D @ V_{GS} = -10V, T_C = 100°C	Continuous Drain Current	-21	
I_{DM}	Pulsed Drain Current ①	-136	
P_D @T_C = 25°C	Maximum Power Dissipation	125	W
	Linear Derating Factor	1.0	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	520	mJ
I_{AR}	Avalanche Current ①	-21	A
E_{AR}	Repetitive Avalanche Energy ①	12.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-3.4	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	9.3 (Typical)	g

For Footnotes refer to the page 2.

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	-100	—	—	V	V_{GS} = 0V, I_D = -250µA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.12	—	V/°C	Reference to 25°C, I_D = -1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	0.07	Ω	V_{GS} = -10V, I_D = -21A ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	V_{DS} = V_{GS}, I_D = -250µA
Gfs	Forward Transconductance	10	—	—	S	V_{DS} = -15V, I_D = -21A ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	-25	µA	V_{DS} = -100V, V_{GS} = 0V
		—	—	-250		V_{DS} = -80V,V_{GS} = 0V,T_J =125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V_{GS} = -20V
	Gate-to-Source Leakage Reverse	—	—	100		V_{GS} = 20V
Q_G	Total Gate Charge	—	—	180	nC	I_D = -21A
Q_{GS}	Gate-to-Source Charge	—	—	25		V_{DS} = -80V
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	100		V_{GS} = -10V
$t_{d(on)}$	Turn-On Delay Time	—	—	28	ns	V_{DD} = -50V
tr	Rise Time	—	—	150		I_D = -21A
$t_{d(off)}$	Turn-Off Delay Time	—	—	100		R_G = 2.5Ω
t_f	Fall Time	—	—	120		V_{GS} = -10V
Ls +L_D	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm / 0.25 in from package) to Source lead (6mm/ 0.25 in from package) with Source wire internally bonded from Source pin to Drain pad
C_{iss}	Input Capacitance	—	2730	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	824	—		V_{DS} = -25V
C_{rss}	Reverse Transfer Capacitance	—	465	—		f = 1.0MHz

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-34	A	
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-136		
V_{SD}	Diode Forward Voltage	—	—	-1.6	V	T_J = 25°C,I_S = -21A, V_{GS} = 0V④
t_{rr}	Reverse Recovery Time	—	—	260	ns	T_J = 25°C, I_F = -21A, V_{DD} ≤ - 30V
Q_{rr}	Reverse Recovery Charge	—	—	1.8	µC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	1.0	°C/W
$R_{\theta CS}$	Case -to-Sink	—	0.21	—	
$R_{\theta JA}$	Junction-to-Ambient (Typical socket mount)	—	—	48	

Footnotes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = -25V, starting T_J = 25°C, L = 2.4mH, Peak I_L = -21A, V_{GS} = -10V,R_G = 25Ω.

③ $I_{SD} \le$ -21A, di/dt ≤ -400A/µs, $V_{DD} \le$ -100V, $T_J \le$ 150°C

④ Pulse width ≤ 300 µs; Duty Cycle ≤ 2%.

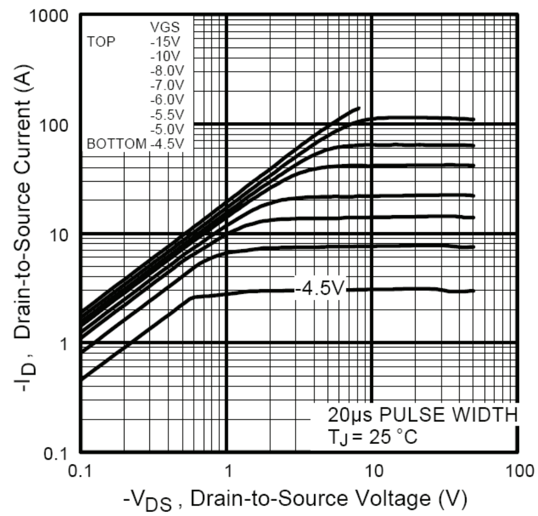


Fig 1. Typical Output Characteristics

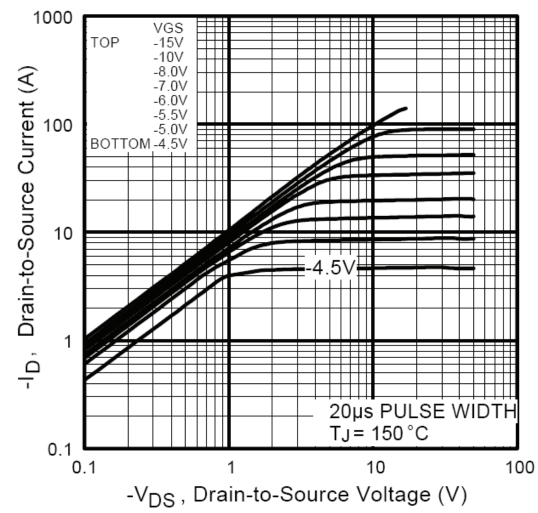


Fig 2. Typical Output Characteristics

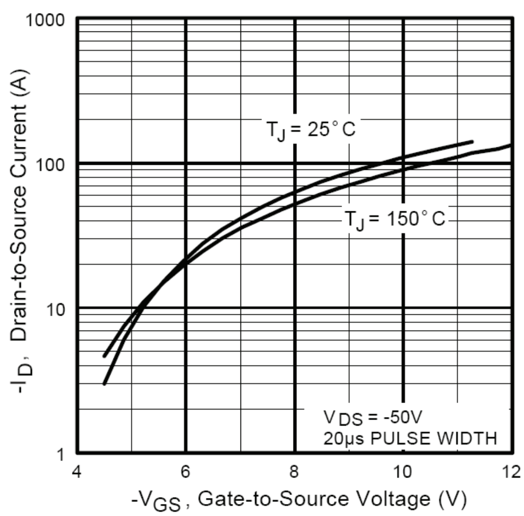


Fig 3. Typical Transfer Characteristics

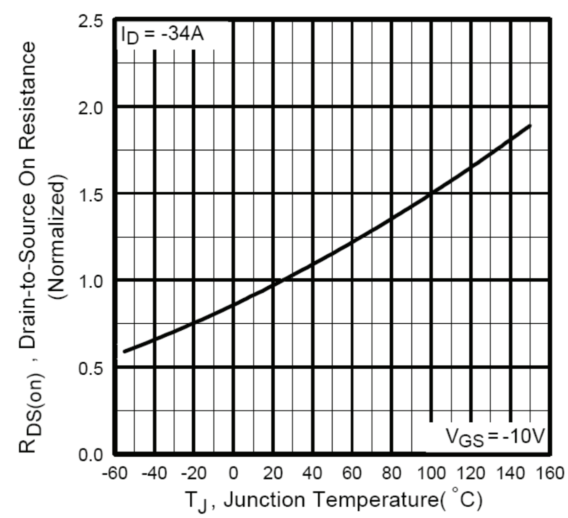


Fig 4. Normalized On-Resistance Vs. Temperature

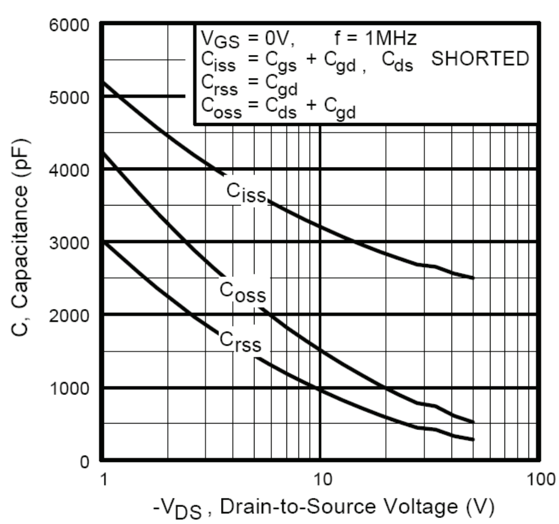


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

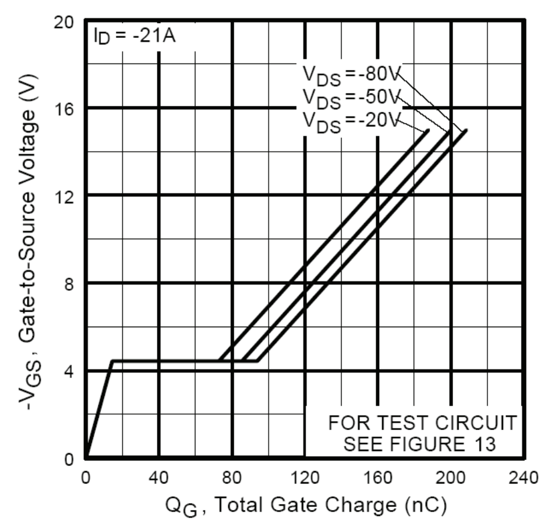


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

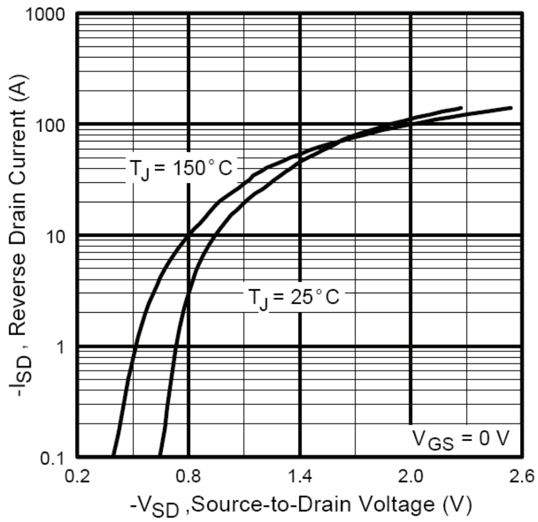


Fig 7. Typical Source-Drain Diode Forward Voltage

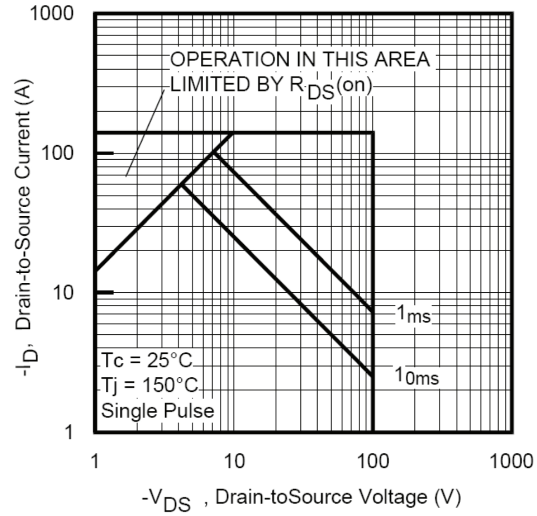


Fig 8. Maximum Safe Operating Area

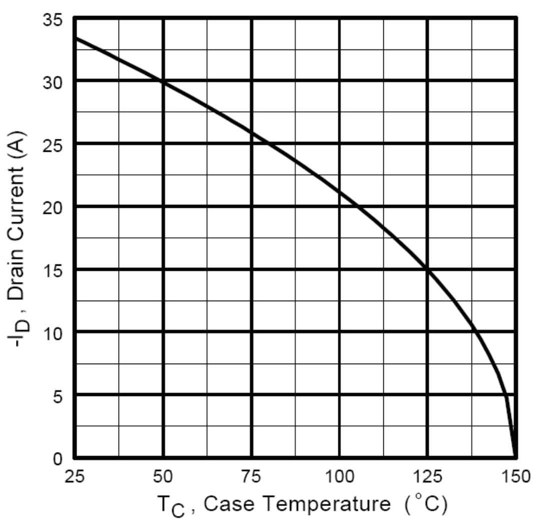


Fig 9. Maximum Drain Current Vs. Case Temperature

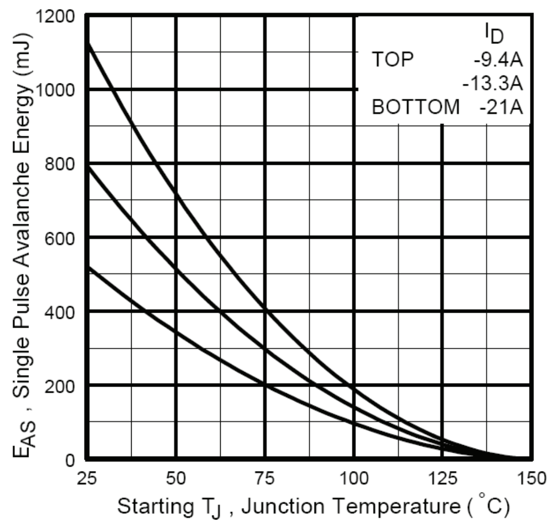


Fig 10. Maximum Avalanche Energy Vs. Drain Current

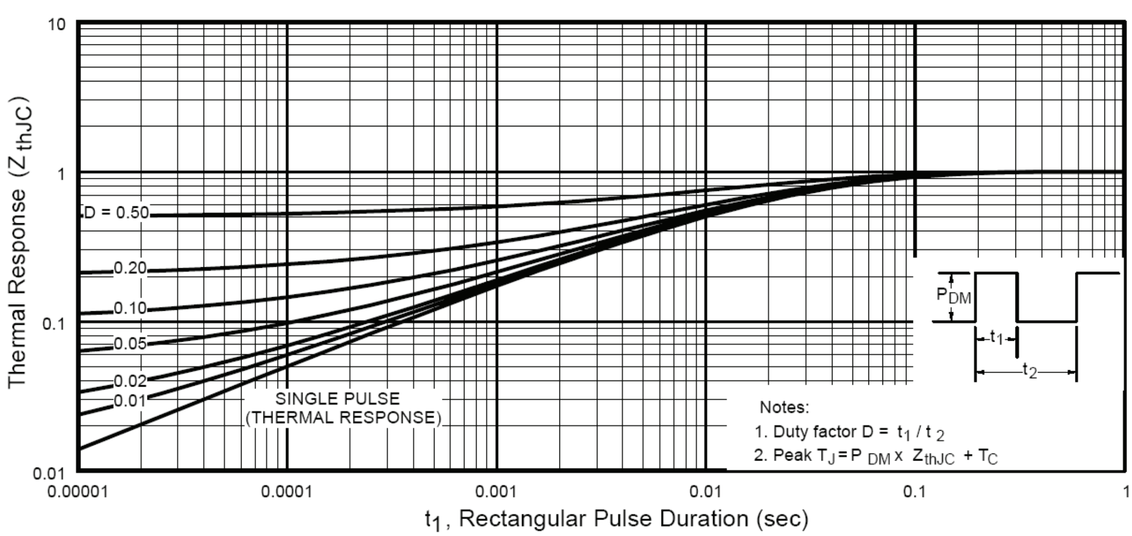


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

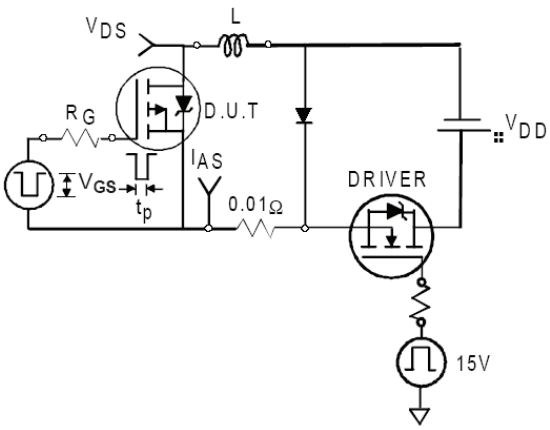


Fig 12a. Unclamped Inductive Test Circuit

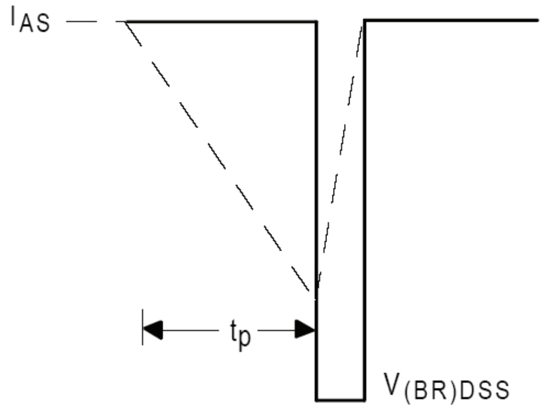


Fig 12b. Unclamped Inductive Waveforms

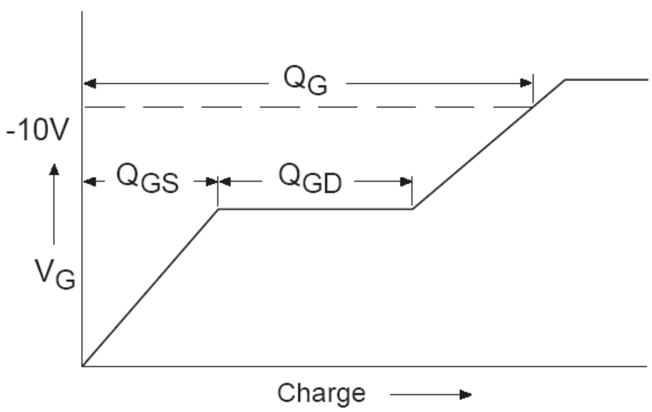


Fig 13a. Basic Gate Charge Waveform

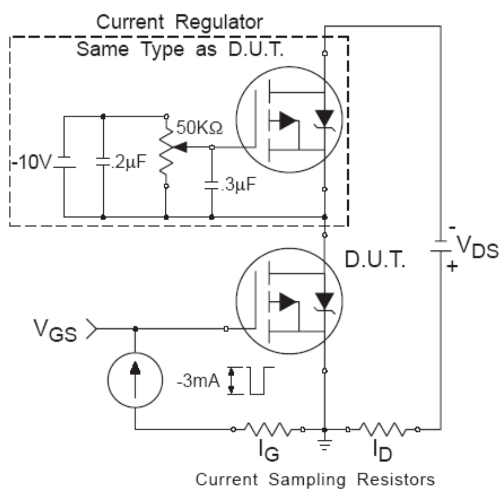


Fig 13b. Gate Charge Test Circuit

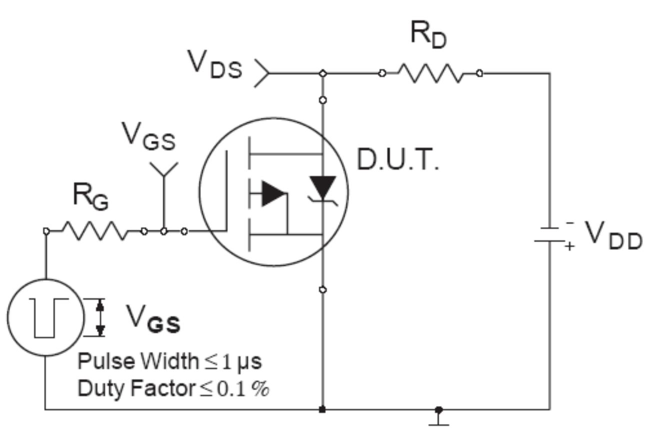


Fig 14a. Switching Time Test Circuit

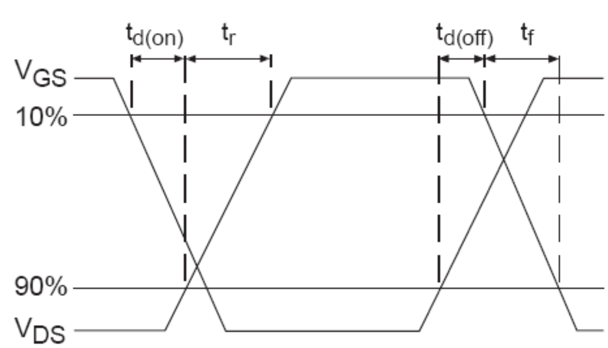
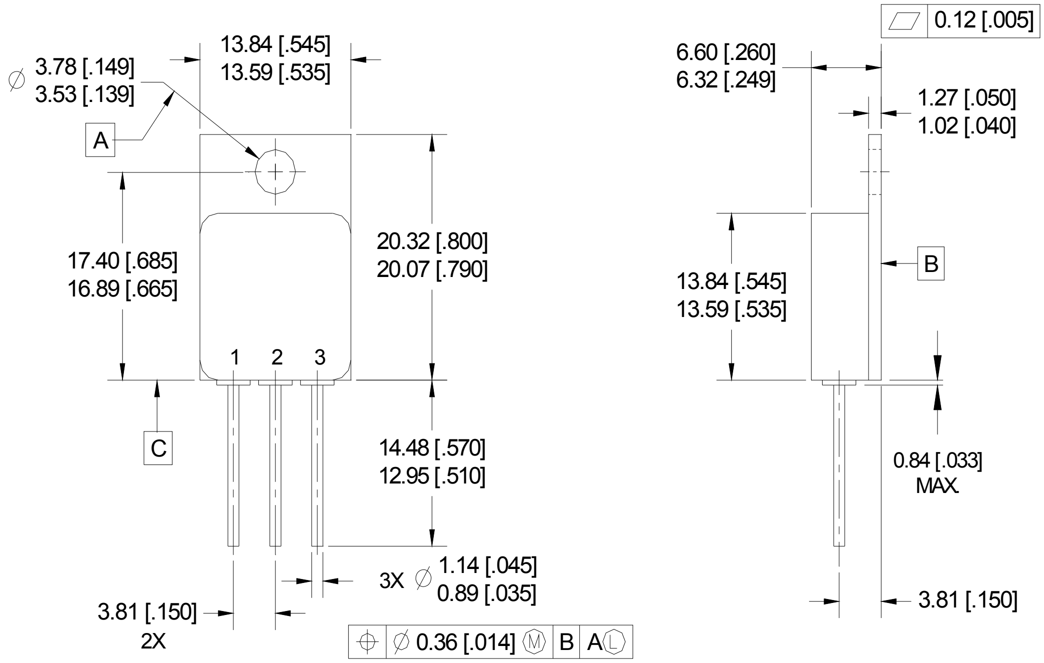


Fig 14b. Switching Time Waveforms

Case Outline and Dimensions — TO-254AA



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. CONTROLLING DIMENSION: INCH.
4. CONFORMS TO JEDEC OUTLINE TO-254AA.

PIN ASSIGNMENTS

1 = DRAIN
2 = SOURCE
3 = GATE

BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

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